



# PSMN3R9-100YSF

NextPower 100 V, 4.3 mΩ N-channel MOSFET in LFPK56 package

17 February 2020

Preliminary data sheet

## 1. General description

NextPower 100 V, standard level gate drive MOSFET. Qualified to 150 °C and recommended for industrial and consumer applications.

## 2. Features and benefits

- Low  $Q_{rr}$  for higher efficiency and lower spiking
- 120 A  $I_D$  (max) – demonstrated continuous current rating
- Low  $Q_G \times R_{DSon}$  FOM for high efficiency switching applications
- Strong avalanche energy rating ( $E_{as}$ )
- Avalanche rated and 100% tested
- Ha-free and RoHS compliant LFPK56 package
- Wave-solderable LFPK56 package

## 3. Applications

- Synchronous rectifier in AC-DC and DC-DC
- Primary side switch – 48 V DC-DC
- BLDC motor control
- USB-PD adapters
- Full-bridge and half-bridge applications
- Flyback and resonant topologies

## 4. Quick reference data

Table 1. Quick reference data

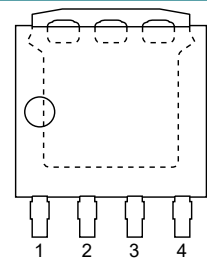
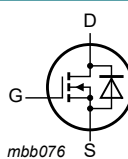
| Symbol                         | Parameter                        | Conditions  | Min | Typ  | Max  | Unit |
|--------------------------------|----------------------------------|---|-----|------|------|------|
| $V_{DS}$                       | drain-source voltage             | $25\text{ °C} \leq T_j \leq 150\text{ °C}$  | -   | -    | 100  | V    |
| $I_D$                          | drain current                    | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ <a href="#">Fig. 2</a>                             | -   | -    | 120  | A    |
| $P_{tot}$                      | total power dissipation          | $T_{mb} = 25\text{ °C};$ <a href="#">Fig. 1</a>   | -   | -    | 245  | W    |
| $T_j$                          | junction temperature             |   | -55 | -    | 150  | °C   |
| <b>Static characteristics</b>  |                                  |   |     |      |      |      |
| $R_{DSon}$                     | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ <a href="#">Fig. 10</a>            | -   | 3.3  | 4.3  | mΩ   |
|                                |                                  | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 100\text{ °C};$ <a href="#">Fig. 11</a>           | -   | 5.1  | 6.9  | mΩ   |
| <b>Dynamic characteristics</b> |                                  |   |     |      |      |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 25\text{ A}; V_{DS} = 50\text{ V}; V_{GS} = 10\text{ V};$ <a href="#">Fig. 12; Fig. 13</a> | -   | 15.8 | 35.6 | nC   |
| $Q_{G(tot)}$                   | total gate charge                |   | -   | 79   | 111  | nC   |

| Symbol                      | Parameter                                    | Conditions   | Min | Typ | Max | Unit |
|-----------------------------|--|--|-----|-----|-----|------|
| <b>Avalanche ruggedness</b> |  |  |     |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 55\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped; <a href="#">Fig. 4</a> | [1] | -   | 310 | mJ   |
| <b>Source-drain diode</b>   |  |  |     |     |     |      |
| $Q_r$                       | recovered charge                             | $I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 50\text{ V}$ ; <a href="#">Fig. 16</a>   | -   | 44  | 66  | nC   |

[1] Protected by 100% test

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline   | Graphic symbol  |
|-----|--------|-----------------------------------|--|---|
| 1   | S      | source                            |  <p>LPAK56E; Power-SO8 (SOT1023)</p> |  <p>mbb076</p> |
| 2   | S      | source                            |  |   |
| 3   | S      | source                            |  |   |
| 4   | G      | gate                              |  |   |
| mb  | D      | mounting base; connected to drain |  |   |

## 6. Ordering information

Table 3. Ordering information

| Type number    | Package            |  |         |
|----------------|--------------------|--|---------|
|                | Name               | Description  | Version |
| PSMN3R9-100YSF | LPAK56E; Power-SO8 | plastic, single-ended surface-mounted package (LPAK56); 4 leads; 1.27 mm pitch | SOT1023 |

## 7. Marking

Table 4. Marking codes

| Type number    | Marking code |
|----------------|--------------|
| PSMN3R9-100YSF | 3F9S10J      |

## 8. Limiting values

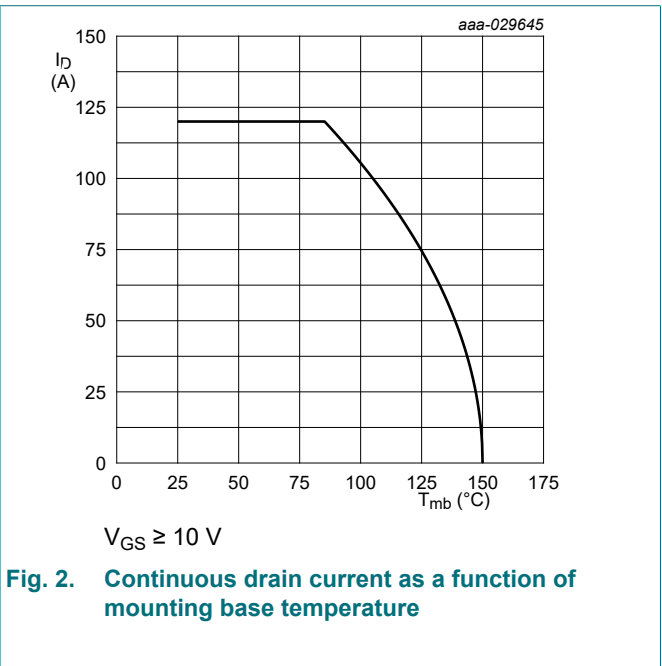
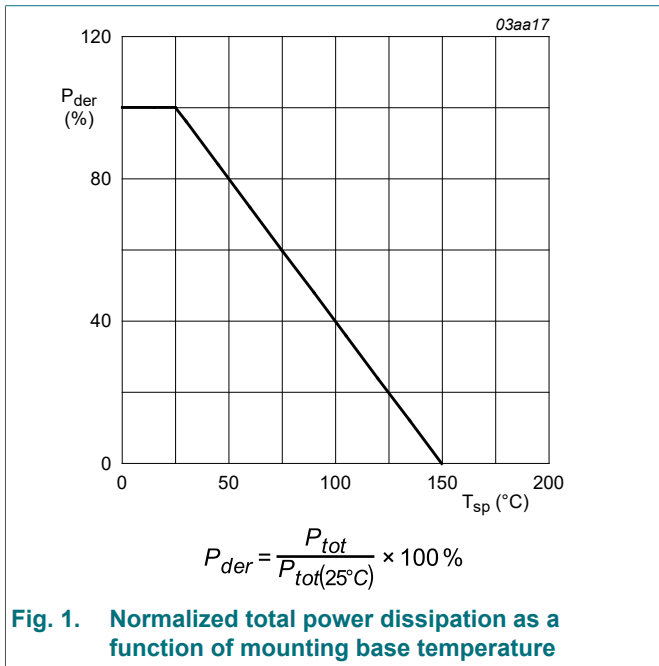
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions  | Min | Max | Unit |
|-----------|-------------------------|---|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $25\text{ }^\circ\text{C} \leq T_j \leq 150\text{ }^\circ\text{C}$                                | -   | 100 | V    |
| $V_{DGR}$ | drain-gate voltage      | $25\text{ }^\circ\text{C} \leq T_j \leq 150\text{ }^\circ\text{C}$ ; $R_{GS} = 20\text{ k}\Omega$ | -   | 100 | V    |
| $V_{GS}$  | gate-source voltage     |   | -20 | 20  | V    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>                                      | -   | 245 | W    |

| Symbol                      | Parameter                                    | Conditions   | Min | Max | Unit   |
|-----------------------------|--|--|-----|-----|--------|
| I <sub>D</sub>              | drain current                                | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>  | -   | 120 | A      |
|                             |  | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <a href="#">Fig. 2</a>   | -   | 105 | A      |
| I <sub>DM</sub>             | peak drain current                           | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 3</a>  | -   | 667 | A      |
| T <sub>stg</sub>            | storage temperature                          |  | -55 | 150 | °C     |
| T <sub>j</sub>              | junction temperature                         |  | -55 | 150 | °C     |
| T <sub>slid(M)</sub>        | peak soldering temperature                   |  | -   | 260 | °C     |
| <b>Source-drain diode</b>   |  |  |     |     |        |
| I <sub>S</sub>              | source current                               | T <sub>mb</sub> = 25 °C  | -   | 120 | A      |
| I <sub>SM</sub>             | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C  | -   | 667 | A      |
| <b>Avalanche ruggedness</b> |  |  |     |     |        |
| E <sub>DS(AL)S</sub>        | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 55 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; <a href="#">Fig. 4</a> | [1] | -   | 310 mJ |
| I <sub>AS</sub>             | non-repetitive avalanche current             | V <sub>sup</sub> = 100 V; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω; <a href="#">Fig. 4</a>                                   | [1] | -   | 55 A   |

[1] Protected by 100% test



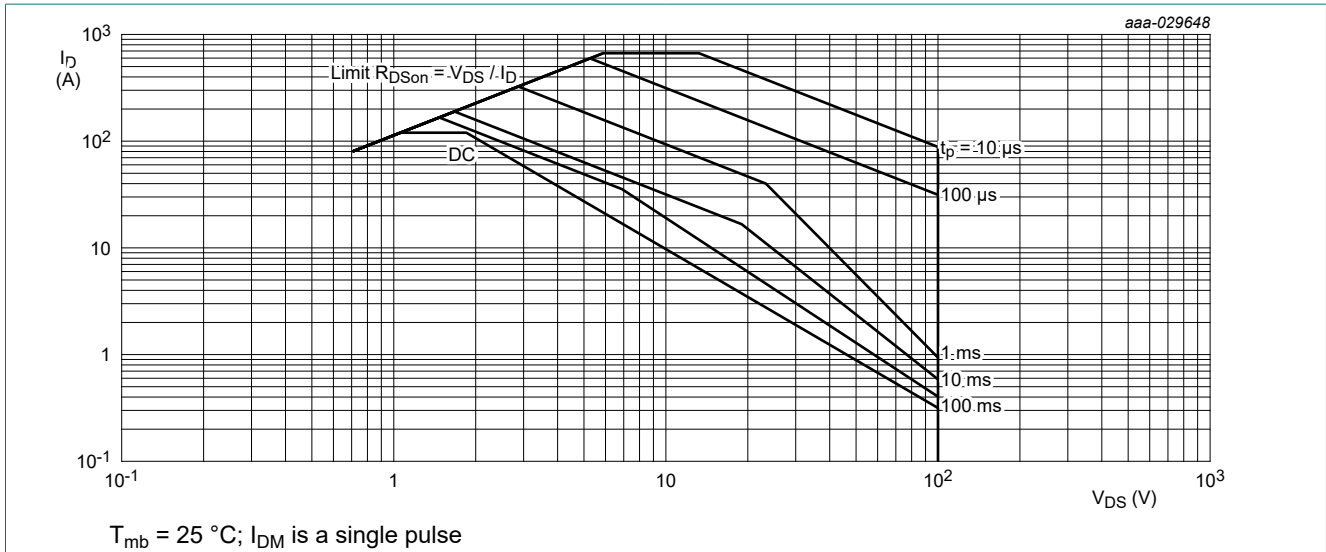


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

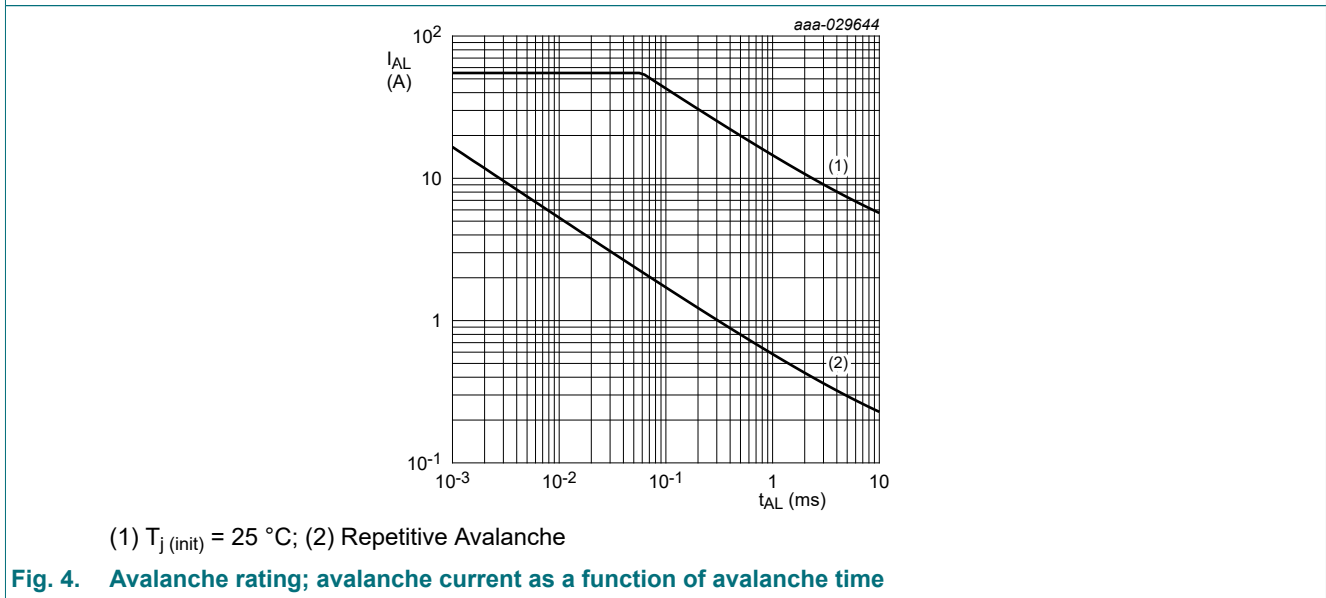


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions | Min | Typ  | Max  | Unit |
|----------------|---|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5     | -   | 0.45 | 0.51 | K/W  |

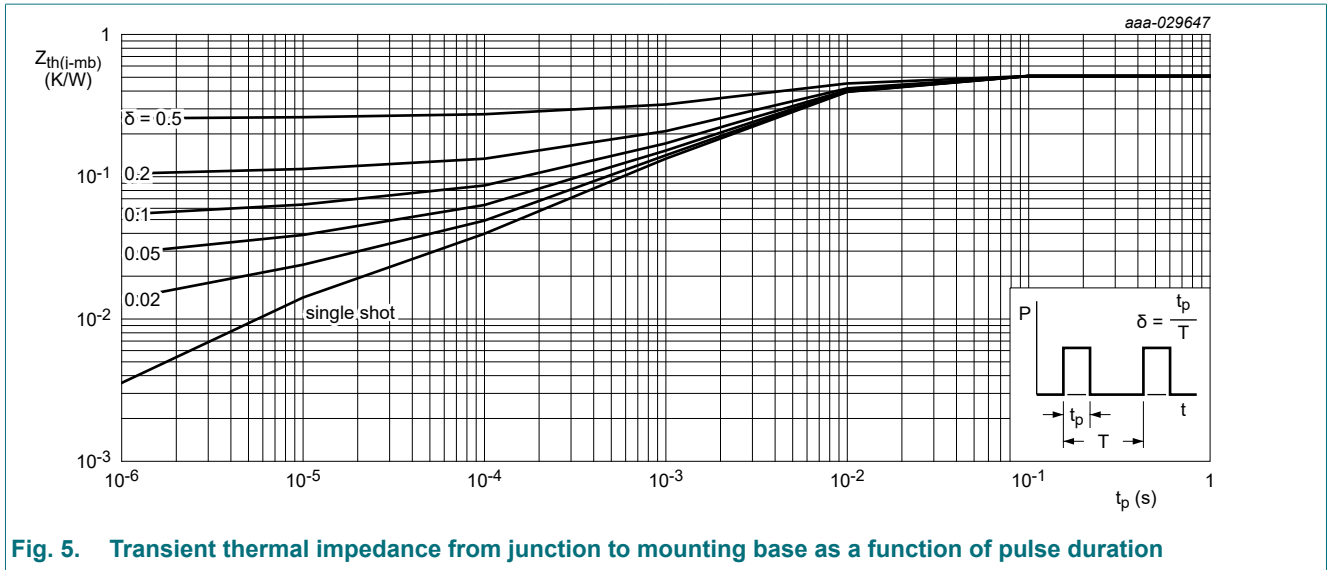


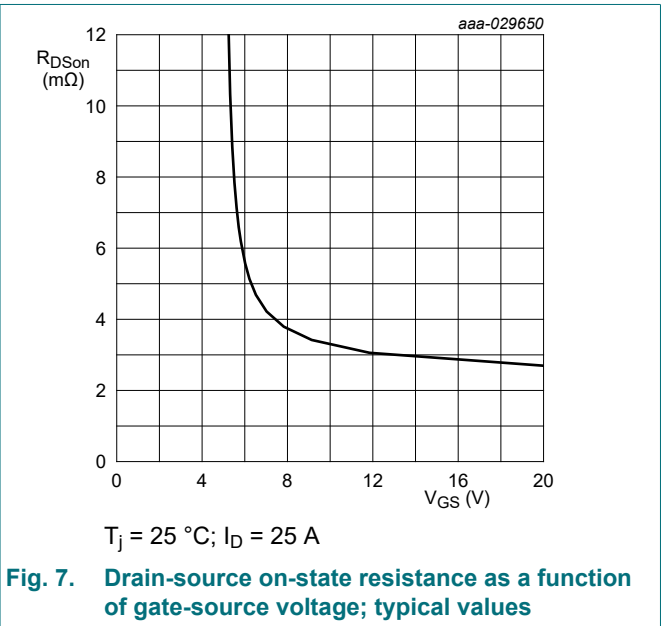
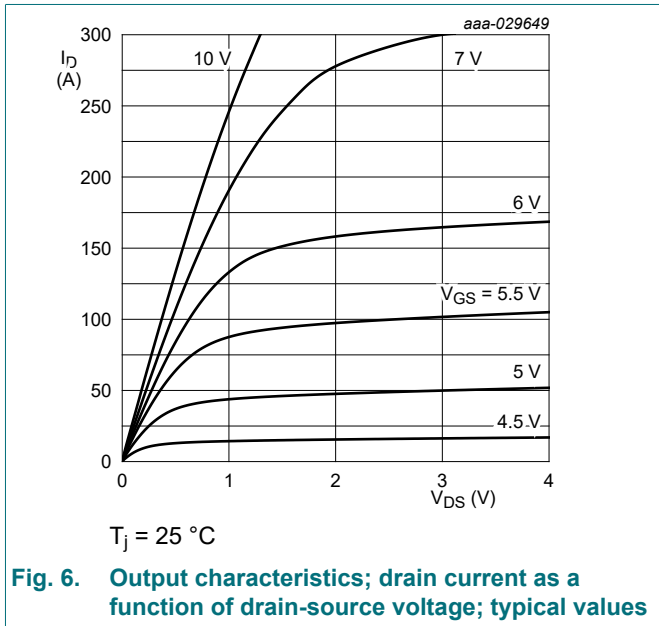
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter  | Conditions   | Min | Typ  | Max | Unit    |
|--------------------------------|--|--|-----|------|-----|---------|
| <b>Static characteristics</b>  |  |  |     |      |     |         |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage                           | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$   | 100 | -    | -   | V       |
|                                |  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$  | 90  | -    | -   | V       |
| $V_{GS(th)}$                   | gate-source threshold voltage                            | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C; \text{ Fig. 9}$                       | 2   | 3    | 4   | V       |
|                                |  | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 150 \text{ }^\circ C$                                      | -   | 1.9  | -   | V       |
|                                |  | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$                                      | -   | 3.5  | -   | V       |
| $\Delta V_{GS(th)}/\Delta T$   | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$   | -   | -8.4 | -   | mV/K    |
| $I_{DSS}$                      | drain leakage current                                    | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                            | -   | 0.03 | 25  | $\mu A$ |
|                                |  | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$                           | -   | -    | 100 | $\mu A$ |
| $I_{GSS}$                      | gate leakage current                                     | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                             | -   | 2    | 100 | nA      |
|                                |  | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                            | -   | 2    | 100 | nA      |
| $R_{DS(on)}$                   | drain-source on-state resistance                         | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C; \text{ Fig. 10}$              | -   | 3.3  | 4.3 | mΩ      |
|                                |  | $V_{GS} = 7 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C; \text{ Fig. 10}$               | -   | 3.9  | 6.1 | mΩ      |
|                                |  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ C; \text{ Fig. 11}$             | -   | 5.1  | 6.9 | mΩ      |
|                                |  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C; \text{ Fig. 11}$             | -   | 6.5  | 8.8 | mΩ      |
| $R_G$                          | gate resistance  | $f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$   | -   | 0.8  | -   | Ω       |
| <b>Dynamic characteristics</b> |  |  |     |      |     |         |
| $Q_{G(tot)}$                   | total gate charge  | $I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}; \text{ Fig. 12}; \text{ Fig. 13}$ | -   | 79   | 111 | nC      |
|                                |  | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$                                     | -   | 42.4 | -   | nC      |

| Symbol                    | Parameter                         | Conditions  | Min  | Typ  | Max  | Unit |
|---------------------------|-----------------------------------|---|------|------|------|------|
| $Q_{GS}$                  | gate-source charge                | $I_D = 25\text{ A}; V_{DS} = 50\text{ V}; V_{GS} = 10\text{ V};$<br><a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>             | -    | 23.6 | 33.1 | nC   |
| $Q_{GS(th)}$              | pre-threshold gate-source charge  |   | -    | 15.3 | -    | nC   |
| $Q_{GS(th-pl)}$           | post-threshold gate-source charge |   | -    | 8.3  | -    | nC   |
| $Q_{GD}$                  | gate-drain charge                 |   | -    | 15.8 | 35.6 | nC   |
| $V_{GS(pl)}$              | gate-source plateau voltage       | $I_D = 25\text{ A}; V_{DS} = 50\text{ V};$ <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>                                      | -    | 4.5  | -    | V    |
| $C_{iss}$                 | input capacitance                 | $V_{DS} = 50\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$<br>$T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 14</a>       | 3963 | 5662 | 7360 | pF   |
| $C_{oss}$                 | output capacitance                |   | 656  | 1313 | 1969 | pF   |
| $C_{rss}$                 | reverse transfer capacitance      |   | 0    | 23   | 52.3 | pF   |
| $t_{d(on)}$               | turn-on delay time                | $V_{DS} = 50\text{ V}; R_L = 2\text{ }^\Omega; V_{GS} = 10\text{ V};$<br>$R_{G(ext)} = 5\text{ }^\Omega$                          | -    | 22   | 33   | ns   |
| $t_r$                     | rise time                         |   | -    | 18   | 25   | ns   |
| $t_{d(off)}$              | turn-off delay time               |   | -    | 45   | 63   | ns   |
| $t_f$                     | fall time                         |   | -    | 23   | 37   | ns   |
| <b>Source-drain diode</b> |                                   |   |      |      |      |      |
| $V_{SD}$                  | source-drain voltage              | $I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 15</a>                                 | -    | 0.82 | 1.2  | V    |
| $t_{rr}$                  | reverse recovery time             | $I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$<br>$V_{DS} = 50\text{ V};$ <a href="#">Fig. 16</a> | -    | 43   | 51   | ns   |
| $Q_r$                     | recovered charge                  |   | -    | 44   | 66   | nC   |



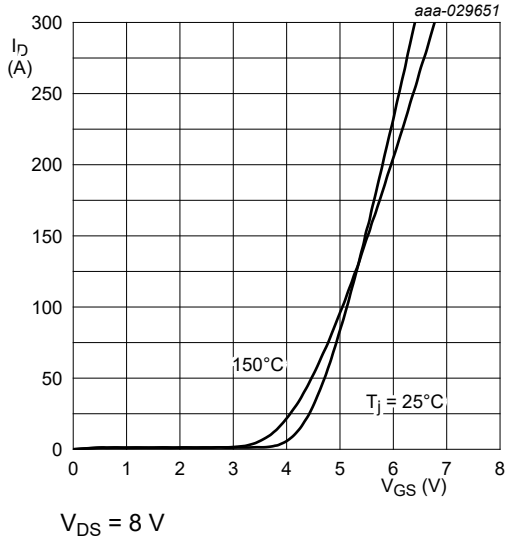


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

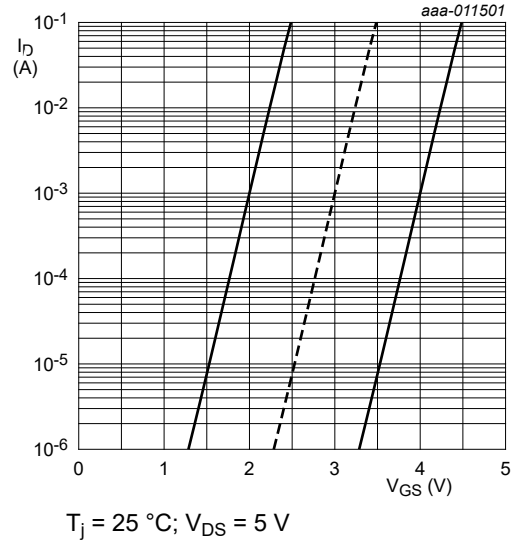


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

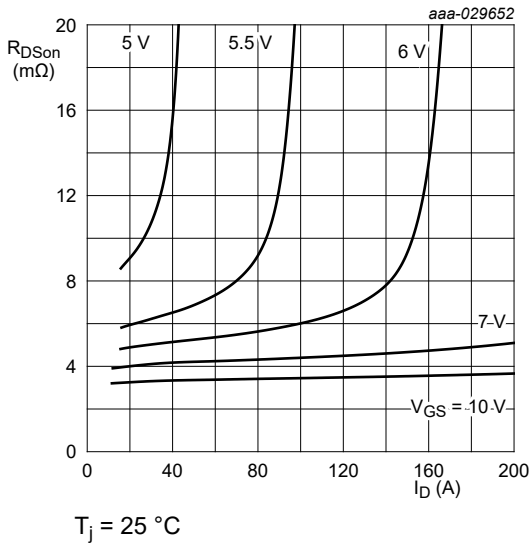


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

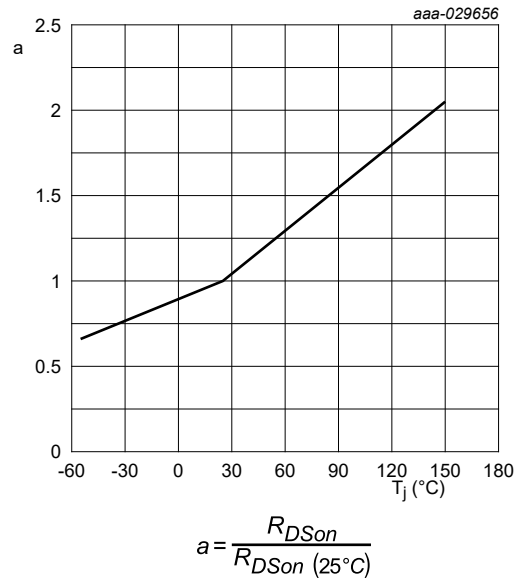


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

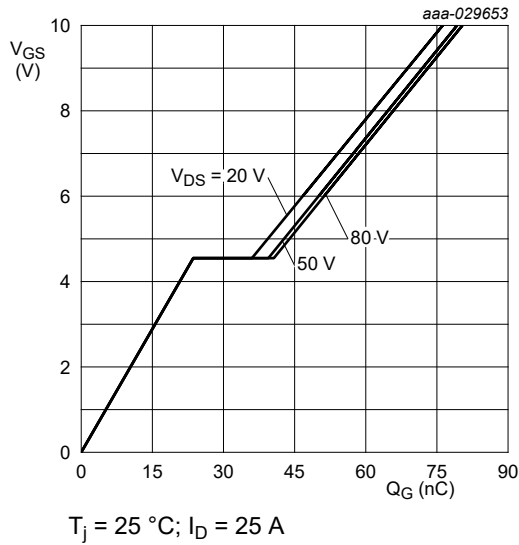


Fig. 12. Gate-source voltage as a function of gate charge; typical values

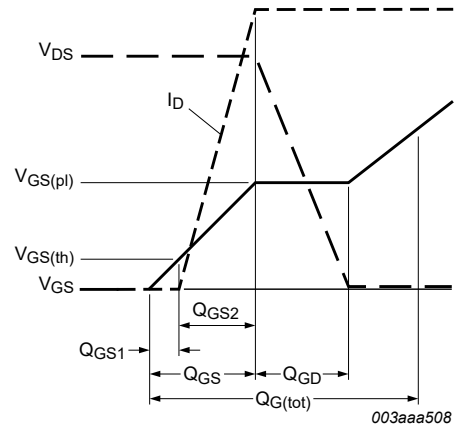


Fig. 13. Gate charge waveform definitions

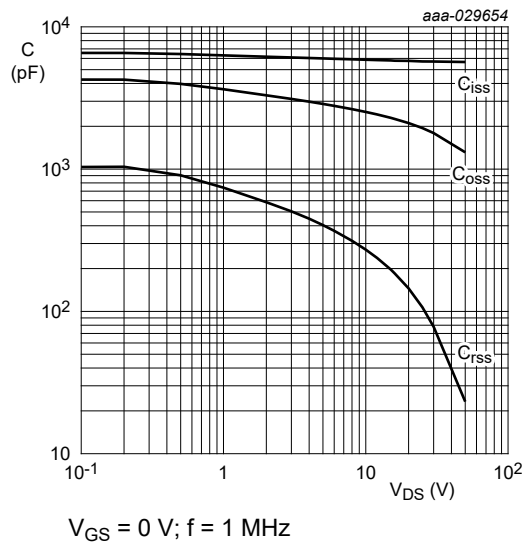


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

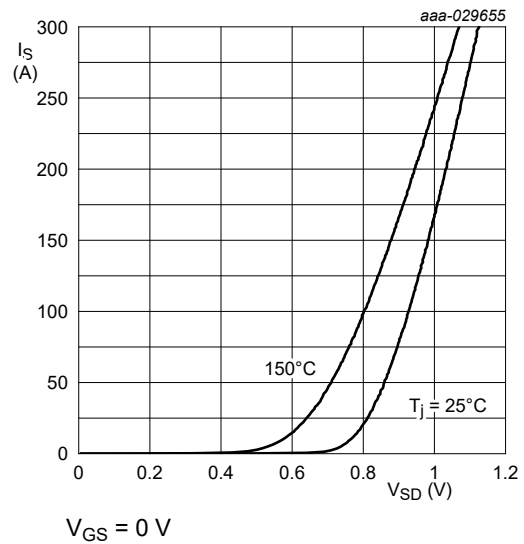


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

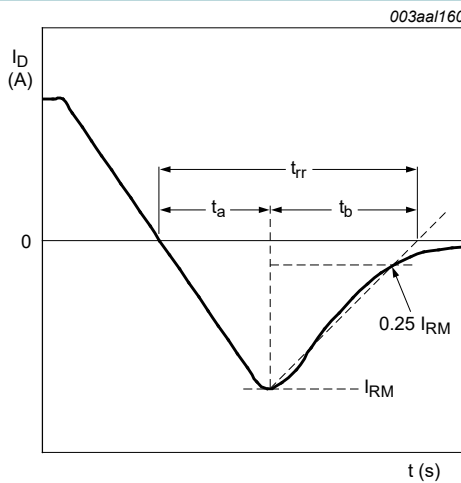


Fig. 16. Reverse recovery timing definition



### 11. Package outline

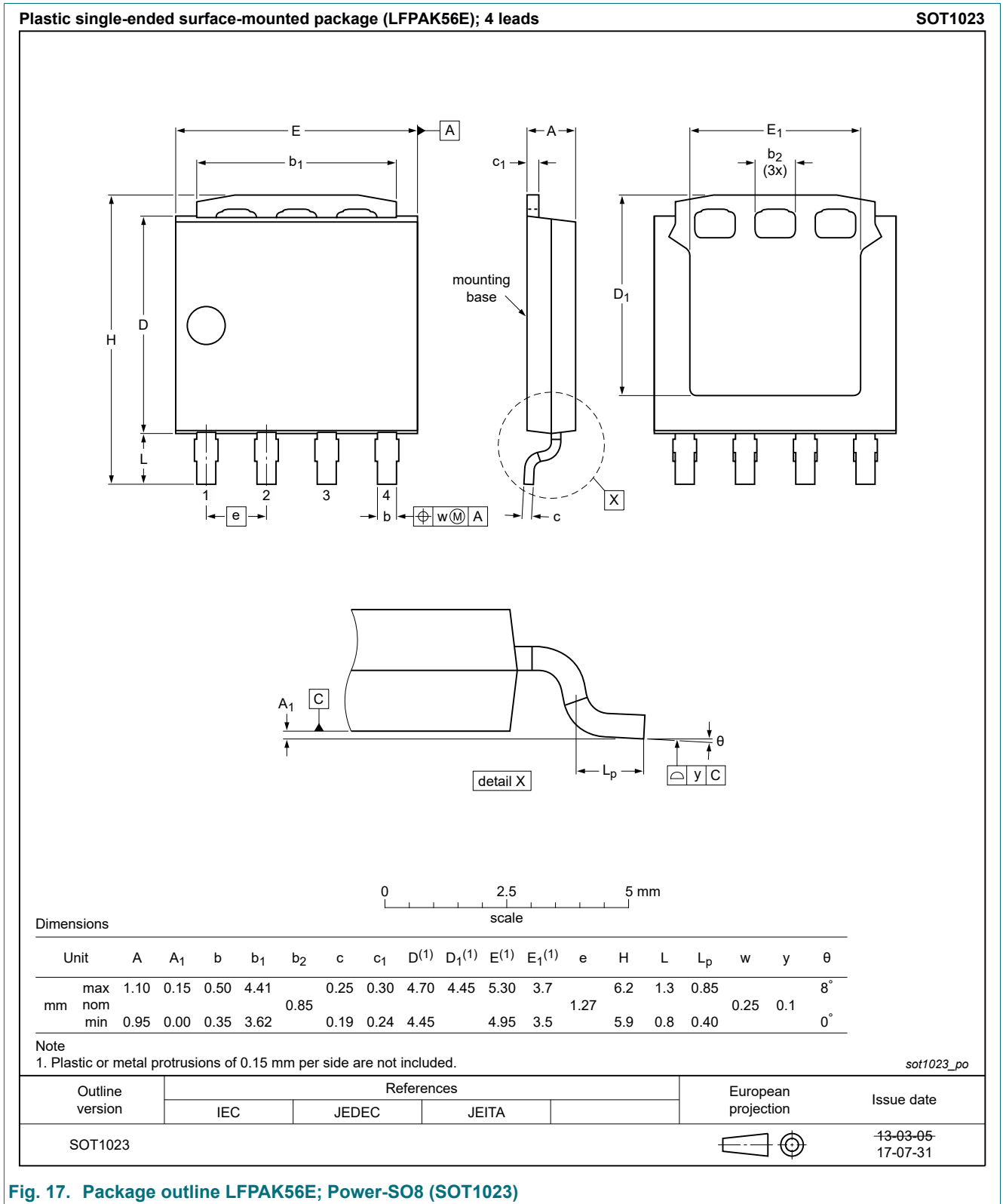


Fig. 17. Package outline LPAK56E; Power-SO8 (SOT1023)

## 12. Soldering

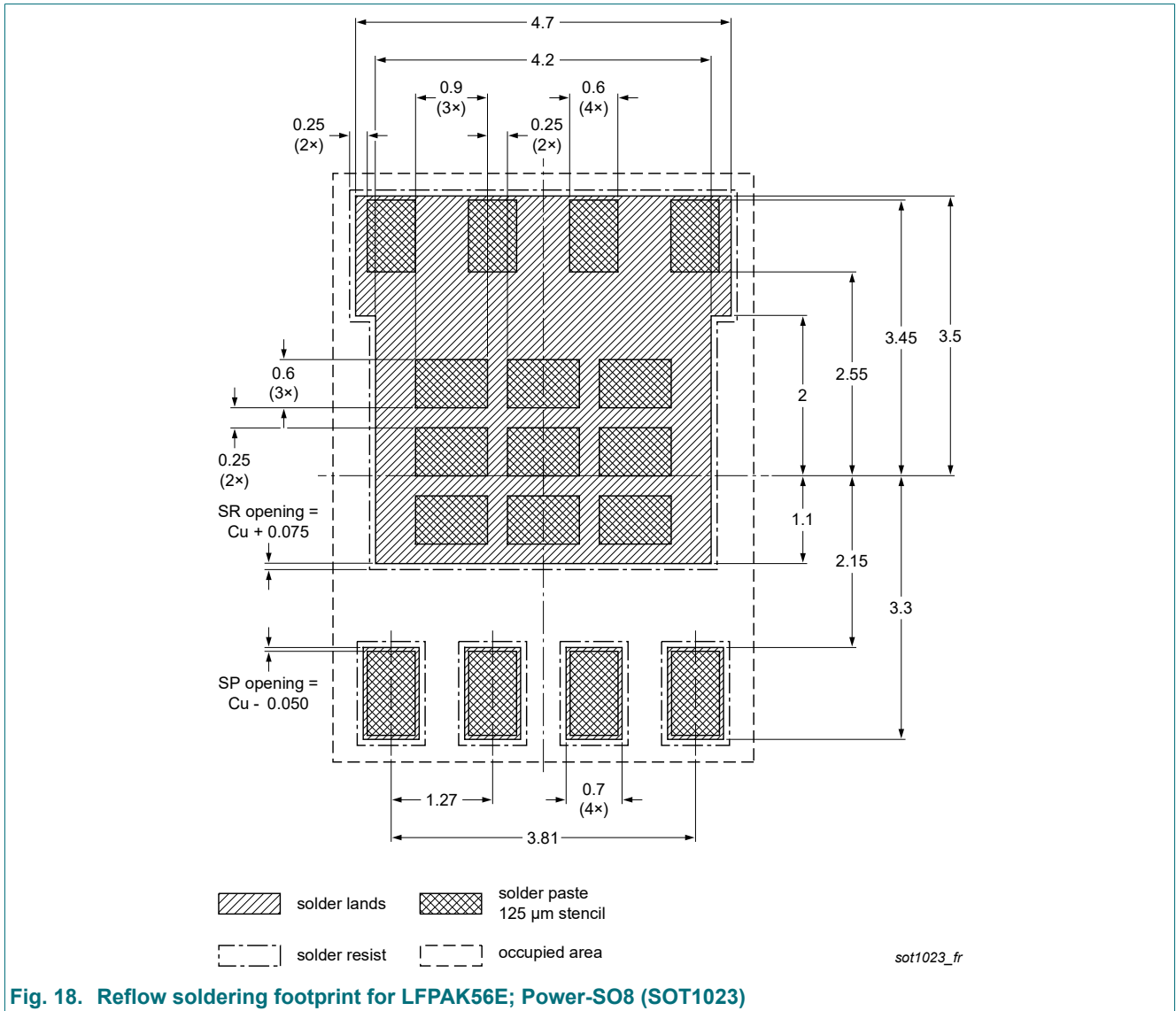


Fig. 18. Reflow soldering footprint for LPAK56E; Power-SO8 (SOT1023)

## 13. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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